NOTICE

The International Joint Workshop on Nitride Semiconductors and Devices is a major academic workshop in the field of wide band gap semiconductors research. It presents high-impact scientific and technological advances in materials and devices based on nitride semiconductors. The first international joint workshop was started by NIT in 2008 in Nagoya and followed by in Beijing (2009), Singapore (2010), Xi`an (2011), Guangzhou (2012), Sanya (2013). After two year`s pause, the 7th workshop will return back to Nagoya and be held on April 11 (Mon.), 2016.

We sincerely invite you to join the workshop organized by Nagoya Institute of Technology. The key time points of the workshop are listed as follows:

Before Dec. 10, 2015: Report title providing
Before Jan. 15, 2016: One page abstract providing
Apr. 01, 2016: Program announcement
Apr. 11, 2016: Workshop and Lab tour
(Venue: Innovation Center for Multi-Business of Nitride Semiconductors,
Gokiso-cho, Showa-ku, Nagoya Institute of Technology, Nagoya, Aichi, Japan)

We appreciate your kind support and look forward to your participation.

Prof. Takashi Egawa
Nagoya Institute of Technology, Japan
April 2016

Program Schedule: April 11, 2016

12:00: Workshop Registration

12:30-12:50

Ta/Si-based Non-Gold Ohmic Contacts for GaN HEMTs on Si, G. I. Ng and S. Arulkumaran, Nanyang Technological University, Singapore

12:50-13:10

Selective Area Growth: A promising way towards stable trench gate E-mode GaN MOSFET on Si substrate, Yang Liu, Baijun Zhang, Sun Yat-sen University, China

13:10-13:30

Breakdown electric field of each layer in AlGaN/GaN high-electron-mobility transistors on Si substrates, Yuya Yamaoka, Kazuhiro Ito, Akinori Ubukata, Toshiya Tabuchi, Koh Matsumoto and Takashi Egawa, Nagoya Institute of Technology, Japan

13:30-13:50

Improved Device Characteristics of AlInN/GaN MOS-HEMTs on Silicon using Atomic Layer deposited Al_2O_3, Joseph. J. Freedsman, Arata Watanabe and Takashi Egawa, Research Center for Nano-Device and System, Nagoya Institute of Technology, Japan

13:50-14-10

Growth of Thick AlN on AlN/Sapphire by Hydride Vapor Phase Epitaxy, H. Miyake, Y. Yamashita, D. Yasui, K. Hiramatsu, M. Iwaya, I. Akasaki, H. Amano, Mie University, Japan

14-10:14:30

Impurity Resonant States p-type Doping in Wide-Band-Gap Nitrides, Zhiqiang Liu, Institute of Semiconductors, CAS, China

14:30-14:50

Development and performance of DUV LED and optical pumped LD, Yun Zhang, Institute of Semiconductors, CAS, China

14:50-15:10 Coffee Break

15:10-15:30

IC technology compatible silicon substrate-based 3-dimensional light emitting devices, Guodong Yuan, Institute of Semiconductors, CAS, China

15:30-15:50

Recent Progress in GaN-LED with ZnO Transparent Conductive Layer, Gang Wang, Bingfeng Fan, Sun Yat-sen University, China

15:50-16:10

High efficiency p-type doping of AlGaN and its application in fabricating high-gain UV photodetectors, Hao Jiang, Sun Yat-sen University, China

16:10-16:30

GaN-based Heterostructures on Si by MBE for HEMT and Photodetector applications, K. Radhakrishnan and L. Ravikiran, N. Dharmarasu, Nanyang Technological University, Singapore

16:30-16:50

Report Title: Not decided, Shuhaimi, University of Malaya

17:00-17:40: Lab tour

18:00-20:00: Reception (Café sala)

窒化物半導体マルチビジネス創生センター（56 号館）

(Innovation Center for Multi-Business of Nitride Semiconductors)